

# FCD600N65S3R0

## MOSFET – Power, N-Channel, SUPERFET III, Easy Drive

**650 V, 6 A, 600 mΩ**

### Description

SUPERFET III MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate.

Consequently, SUPERFET III MOSFET Easy drive series helps manage EMI issues and allows for easier design implementation.

### Features

- 700 V @  $T_J = 150^\circ\text{C}$
- Typ.  $R_{DS(on)} = 493\text{ m}\Omega$
- Ultra Low Gate Charge (Typ.  $Q_g = 11\text{ nC}$ )
- Low Effective Output Capacitance (Typ.  $C_{oss(eff.)} = 127\text{ pF}$ )
- 100% Avalanche Tested
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Applications

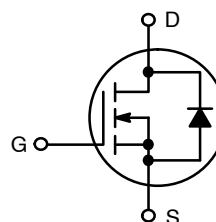
- Computing / Display Power Supplies
- Telecom / Server Power Supplies
- Industrial Power Supplies
- Lighting / Charger / Adapter



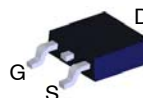
**ON Semiconductor®**

[www.onsemi.com](http://www.onsemi.com)

$V_{DS}$	$R_{DS(on)}\text{ MAX}$	$I_D\text{ MAX}$
650 V	600 mΩ @ 10 V	6 A

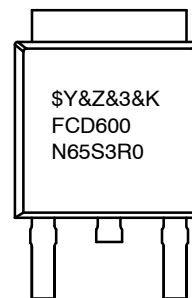


**N-Channel MOSFET**



**D-PAK  
TO-252  
CASE 369AS**

### MARKING DIAGRAM



\$Y	= ON Semiconductor Logo
&Z	= Assembly Plant Code
&3	= Numeric Date Code
&K	= Lot Code
FCD600N65S3R0	= Specific Device Code

### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# FCD600N65S3R0

## ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C, Unless otherwise specified)

Symbol	Parameter		Value	Unit
V <sub>DSS</sub>	Drain to Source Voltage		650	V
V <sub>GSS</sub>	Gate to Source Voltage	DC	±30	V
		AC (f > 1 Hz)	±30	V
I <sub>D</sub>	Drain Current	Continuous (T <sub>C</sub> = 25°C)	6	A
		Continuous (T <sub>C</sub> = 100°C)	3.8	
I <sub>DM</sub>	Drain Current	Pulsed (Note 1)	15	A
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		24	mJ
I <sub>AS</sub>	Avalanche Current (Note 2)		1.6	A
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)		0.54	mJ
dv/dt	MOSFET dv/dt		100	V/ns
	Peak Diode Recovery dv/dt (Note 3)		20	
P <sub>D</sub>	Power Dissipation	(T <sub>C</sub> = 25°C)	54	W
		Derate Above 25°C	0.43	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		–55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 s		300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse-width limited by maximum junction temperature.

2. I<sub>AS</sub> = 1.6 A, R<sub>G</sub> = 25 Ω, starting T<sub>J</sub> = 25°C.

3. I<sub>SD</sub> ≤ 3 A, di/dt ≤ 200 A/μs, V<sub>DD</sub> ≤ 400 V, starting T<sub>J</sub> = 25°C.

## THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R <sub>θJC</sub>	Thermal Resistance, Junction to Case, Max.	2.3	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient, Max. (Note 4)	52	

4. Device on 1 in<sup>2</sup> pad 2 oz copper pad on 1.5 x 1.5 in. board of FR–4 material.

## PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Reel Size	Tape Width	Shipping (Qty / Packing) <sup>†</sup>
FCD600N65S3R0	FCD600N65S3R0	D-PAK (DPAK3 (TO–252 3LD)) (Pb–Free / Halogen Free)	330 mm	16 mm	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# FCD600N65S3R0

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
--------	-----------	-----------------	-----	-----	-----	------

### OFF CHARACTERISTICS

BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 1 mA, T <sub>J</sub> = 25°C	650	–	–	V
		V <sub>GS</sub> = 0 V, I <sub>D</sub> = 1 mA, T <sub>J</sub> = 150°C	700	–	–	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 1 mA, Referenced to 25°C	–	0.66	–	V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V	–	–	1	μA
		V <sub>DS</sub> = 520 V, T <sub>C</sub> = 125°C	–	0.3	–	
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0 V	–	–	±100	nA

### ON CHARACTERISTICS

V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 0.12 mA	2.5	–	4.5	V
R <sub>DS(on)</sub>	Static Drain to Source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3 A	–	493	600	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 20 V, I <sub>D</sub> = 3 A	–	3.6	–	S

### DYNAMIC CHARACTERISTICS

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 400 V, V <sub>GS</sub> = 0 V, f = 1 MHz	–	465	–	pF
C <sub>oss</sub>	Output Capacitance		–	10	–	pF
C <sub>oss(eff.)</sub>	Effective Output Capacitance	V <sub>DS</sub> = 0 V to 400 V, V <sub>GS</sub> = 0 V	–	127	–	pF
C <sub>oss(er.)</sub>	Energy Related Output Capacitance	V <sub>DS</sub> = 0 V to 400 V, V <sub>GS</sub> = 0 V	–	17	–	pF
Q <sub>g(tot)</sub>	Total Gate Charge at 10 V	V <sub>DS</sub> = 400 V, I <sub>D</sub> = 3 A, V <sub>GS</sub> = 10 V (Note 5)	–	11	–	nC
Q <sub>gs</sub>	Gate to Source Gate Charge		–	3	–	nC
Q <sub>gd</sub>	Gate to Drain “Miller” Charge		–	4.9	–	nC
ESR	Equivalent Series Resistance	f = 1 MHz	–	0.9	–	Ω

### SWITCHING CHARACTERISTICS

t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 400 V, I <sub>D</sub> = 3 A, V <sub>GS</sub> = 10 V, R <sub>g</sub> = 4.7 Ω (Note 5)	–	11	–	ns
t <sub>r</sub>	Turn-On Rise Time		–	9	–	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		–	29	–	ns
t <sub>f</sub>	Turn-Off Fall Time		–	14	–	ns

### SOURCE-DRAIN DIODE CHARACTERISTICS

I <sub>S</sub>	Maximum Continuous Source to Drain Diode Forward Current		–	–	6	A
I <sub>SM</sub>	Maximum Pulsed Source to Drain Diode Forward Current		–	–	15	A
V <sub>SD</sub>	Source to Drain Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 3 A	–	–	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 3 A, dI <sub>F</sub> /dt = 100 A/μs	–	198	–	ns
Q <sub>rr</sub>	Reverse Recovery Charge		–	1.6	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Essentially independent of operating temperature typical characteristics.

TYPICAL PERFORMANCE CHARACTERISTICS

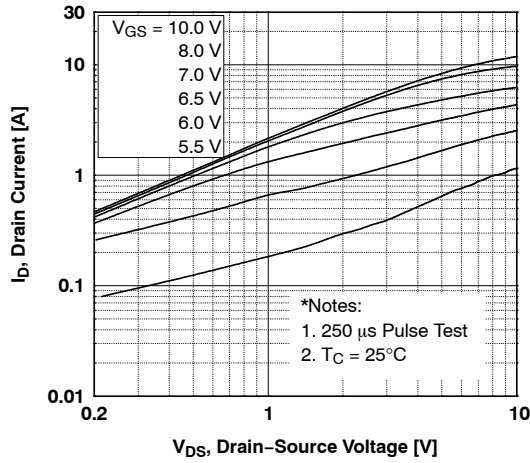


Figure 1. On-Region Characteristics

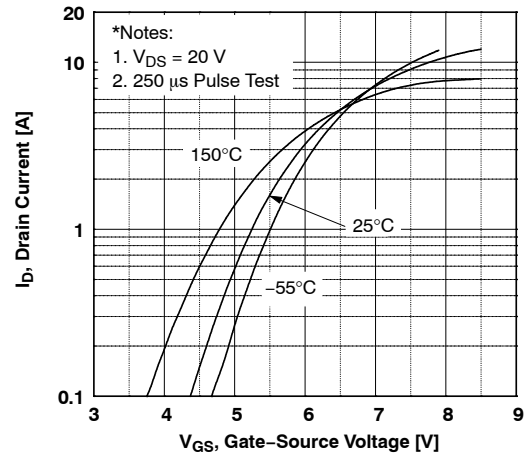


Figure 2. Transfer Characteristics

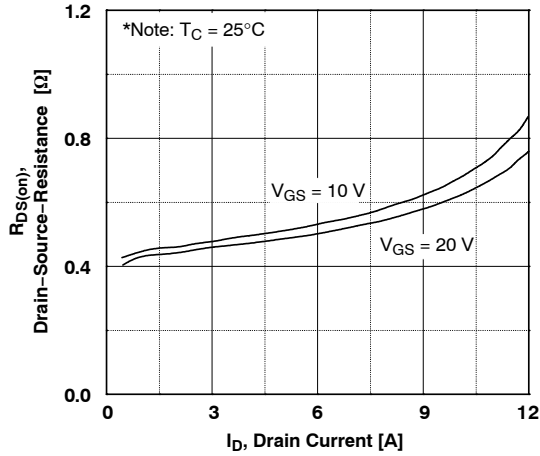


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

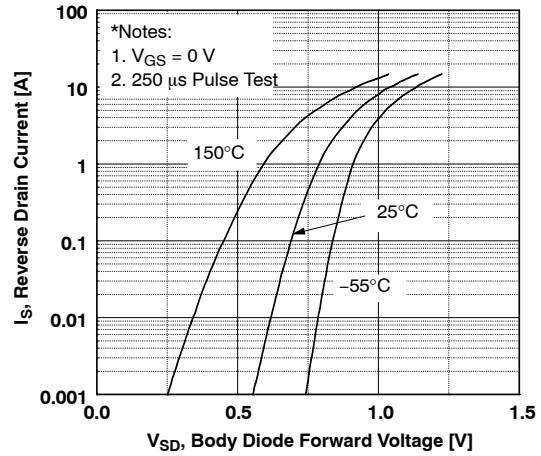


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

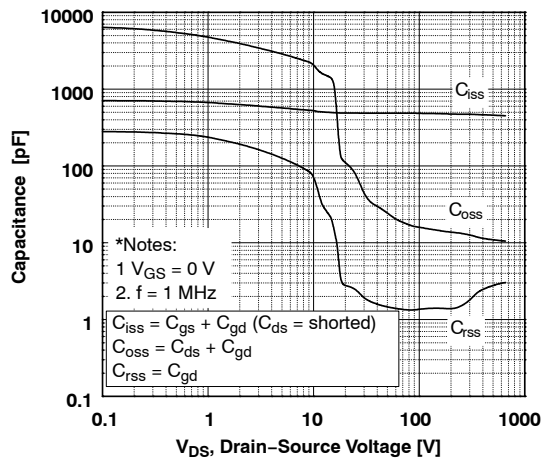


Figure 5. Capacitance Characteristics

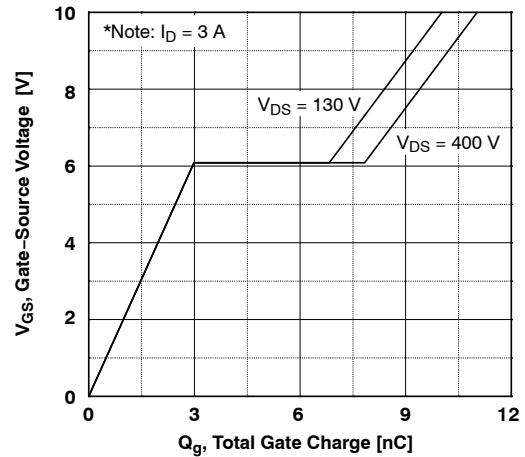


Figure 6. Gate Charge Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

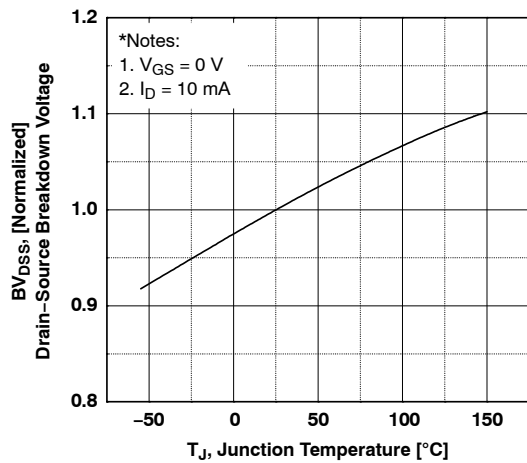


Figure 7. Breakdown Voltage Variation vs. Temperature

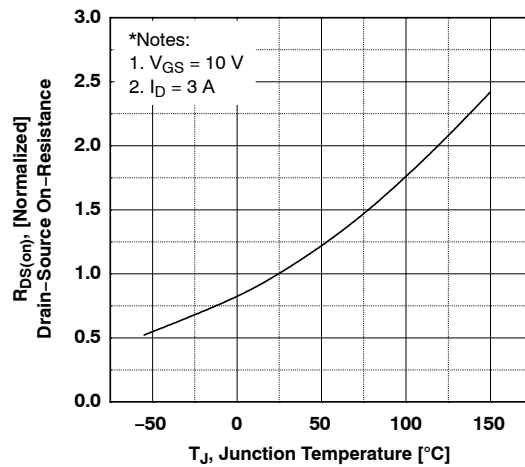


Figure 8. On-Resistance Variant vs. Temperature

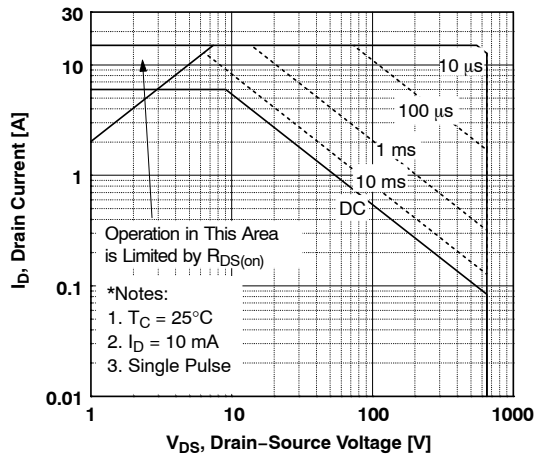


Figure 9. Maximum Safe Operation Area

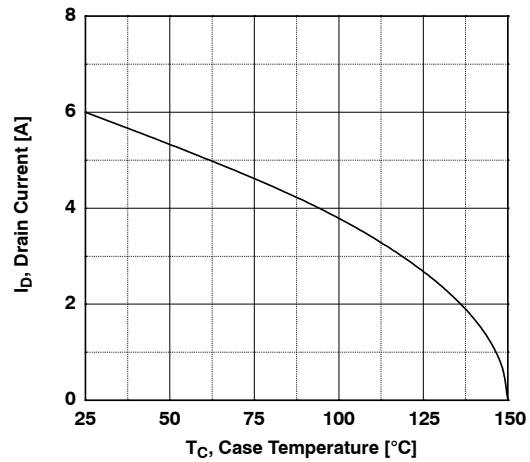


Figure 10. Maximum Drain Current vs. Case Temperature

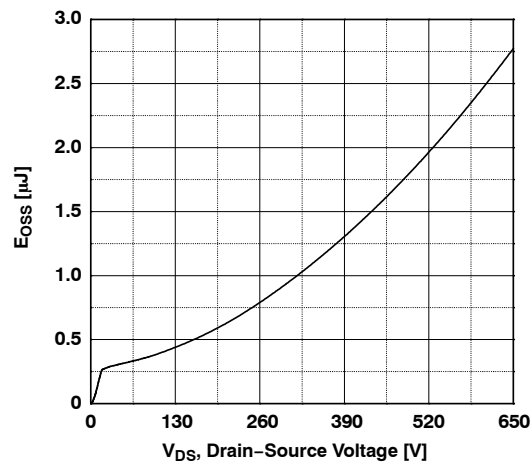


Figure 11.  $E_{OSS}$  vs. Drain to Source Voltage

# FCD600N65S3R0

## TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

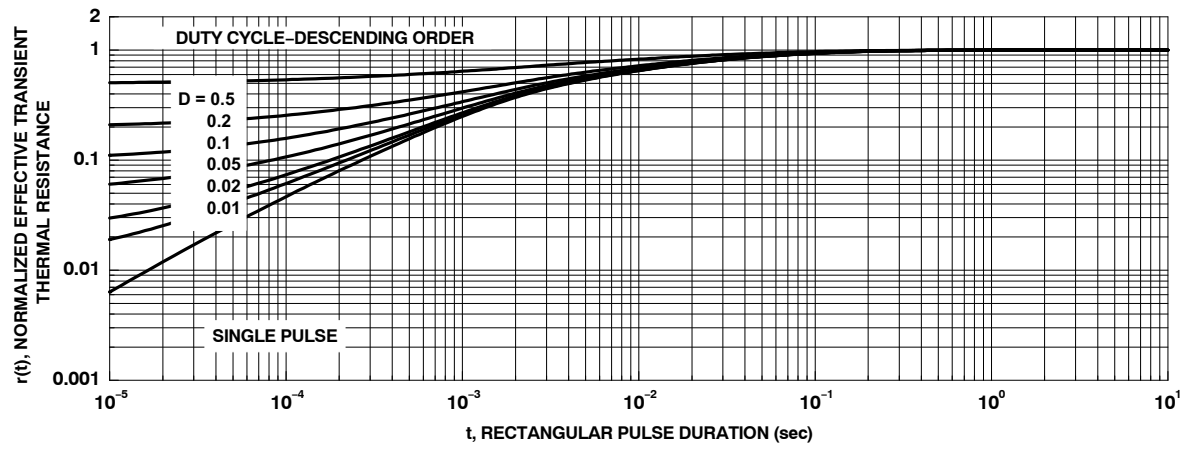


Figure 12. Transient Thermal Response Curve

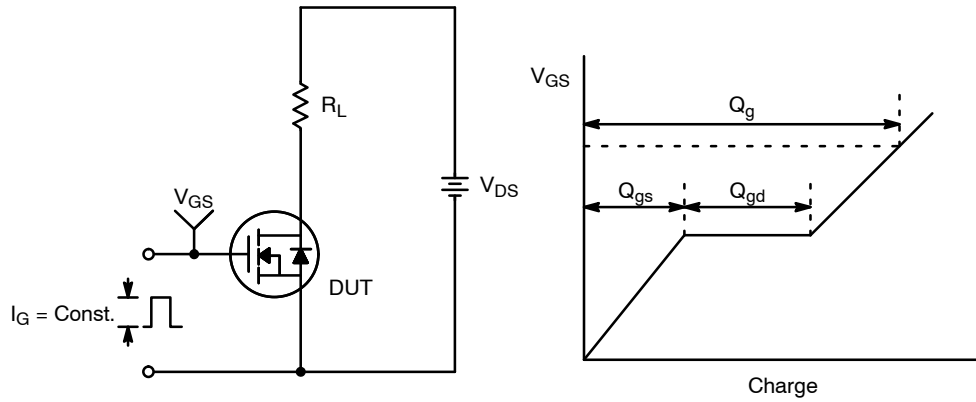


Figure 13. Gate Charge Test Circuit & Waveform

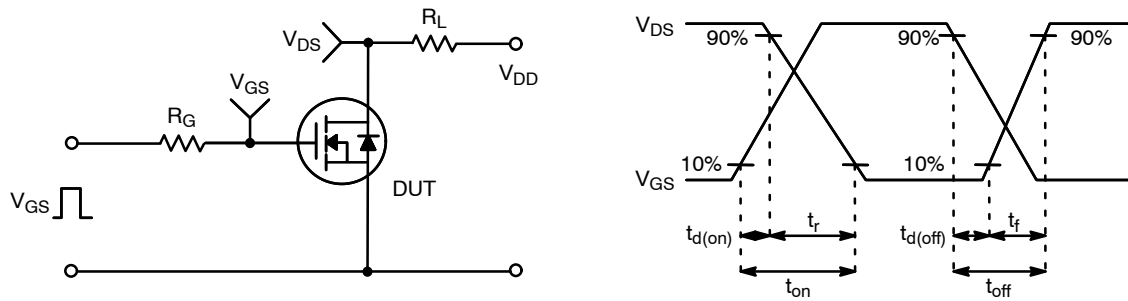


Figure 14. Resistive Switching Test Circuit & Waveforms

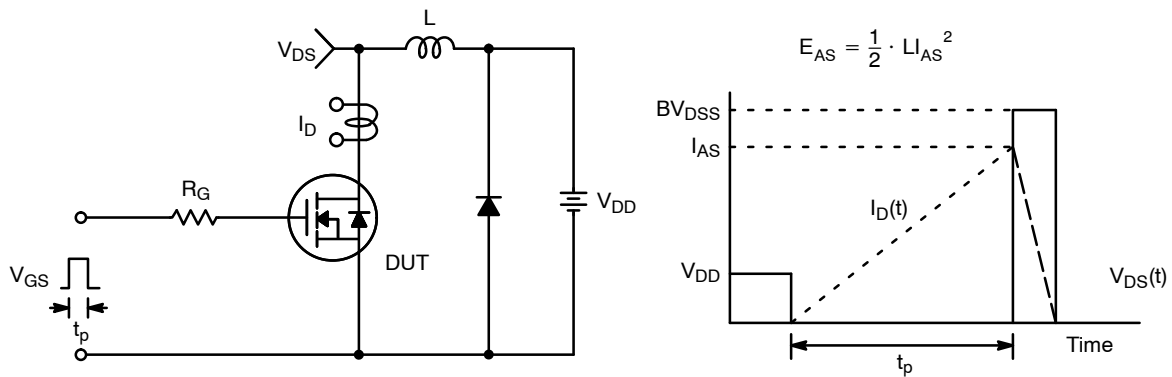
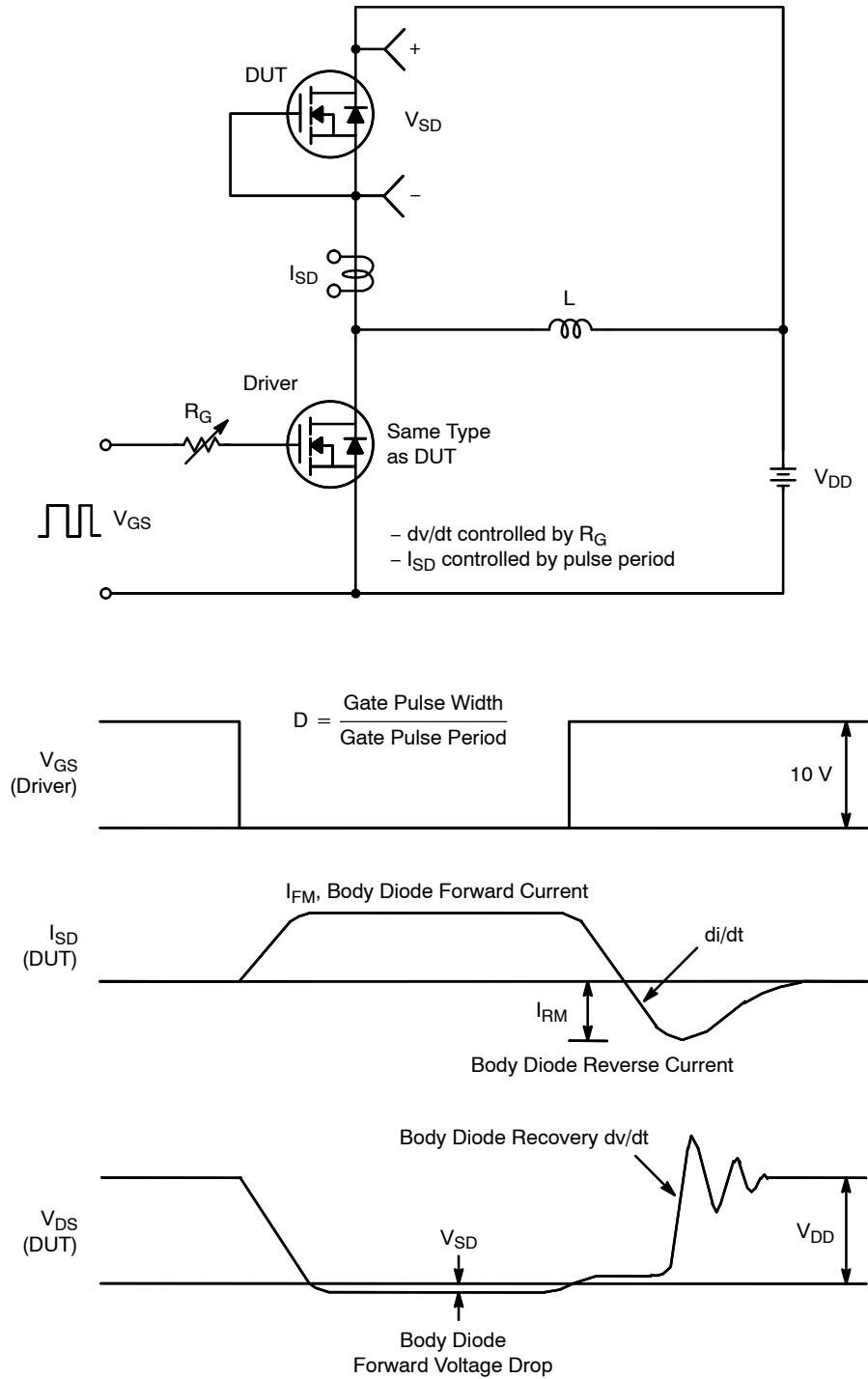


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

# FCD600N65S3R0



**Figure 16. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms**

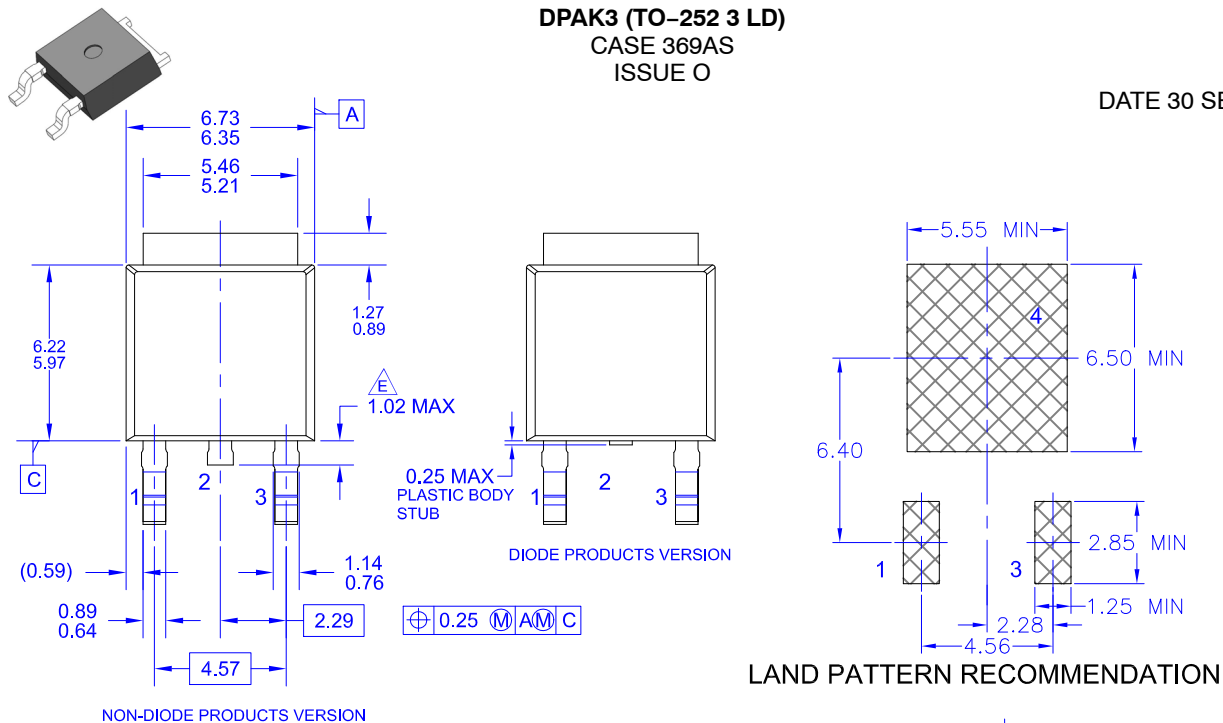


# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



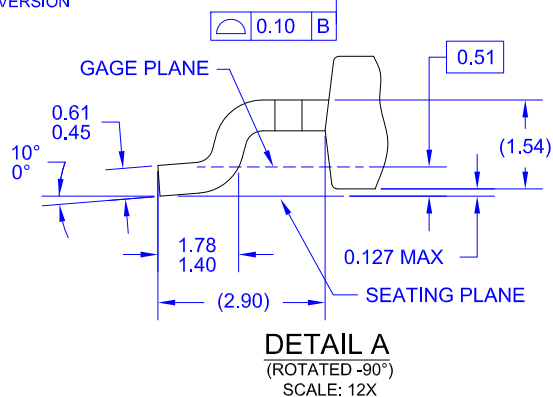
## DPAK3 (TO-252 3 LD) CASE 369AS ISSUE O

DATE 30 SEP 2016



### NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
- D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
- E) TRIMMED CENTER LEAD IS PRESENT ONLY FOR DIODE PRODUCTS
- F) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
- G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.



DOCUMENT NUMBER:	98AON13810G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	DPAK3 (TO-252 3 LD)	PAGE 1 OF 1

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

**onsemi**, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Email Requests to: [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

**onsemi Website:** [www.onsemi.com](http://www.onsemi.com)

### TECHNICAL SUPPORT

**North American Technical Support:**

Voice Mail: 1 800-282-9855 Toll Free USA/Canada

Phone: 011 421 33 790 2910

**Europe, Middle East and Africa Technical Support:**

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative